Supporting Information

Hammering Ag₂Se thermoelectric materials into complex conformal shape with maintained Harman zT

Jun Peng^{1, a, *}, Jianxu Shi^{2, 1, a}, Yusen Ma¹, Yikun Liu¹, Zaifei Cui², Yifeng Zheng³, G.

- 5 Jeffrey Snyder^{4, *}
 - ¹ School of Mechanical Engineering, Xi'an Jiaotong University, Xi'an, Shaanxi, 710049, China
 - ² School of Automation, Xi'an University of Posts and Telecommunications, Xi'an Shaanxi, 710121, China
- 10 ³ School of Physics, Xi'an Jiaotong University, Xi'an, Shaanxi, 710049, China
 - ⁴ Department of Materials Science and Engineering, Northwestern University, Evanston, IL 60208, USA
 - * Corresponding author. E-mail address: jeff.snyder@northwestern.edu
 - ^a These authors contributed equally to this work.

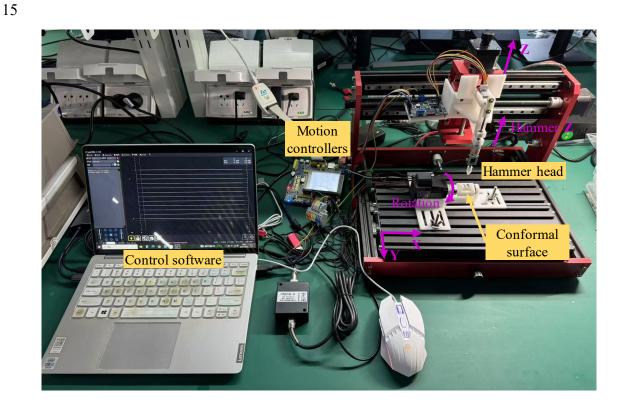


Fig. S1. Home-made hammering equipment.



Fig. S2. Home-made Harman *zT* platform.

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$$S_t = S_g + \left(S_{gb} - S_g\right) \frac{\Delta T_{gb}}{\Delta T_t} \tag{S1}$$

Here, S_t is total Seebeck coefficient of the Ag₂Se sample, S_g is Seebeck coefficient of the Ag₂Se single crystal. S_{gb} is Seebeck coefficient of the Ag₂Se grain boundary phase.

$$S_{gb} = S_g + \left(S_t - S_g\right) \frac{k_g}{k_g - k_t} \tag{S2}$$

Here, S_g and k_g are Seebeck coefficient and thermal conductivity of Ag₂Se single crystal, which are measured and its values are based on references. Corresponding S_t and k_t are those of Ag₂Se polycrystalline.

$$\frac{\Delta T_{gb}}{\Delta T_t} = \frac{1}{\frac{d}{k_g \rho_{Kanitza}} + 1}$$
 (S3)

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$$\rho_{Kapitza} = d\left(\frac{1}{k_t} - \frac{1}{k_g}\right)$$
 (S4)

Here, d is average grain size.

$$\sigma_t = \frac{\sigma_g}{1 + \frac{\rho_{el-gb}\sigma_g}{d}} \tag{S5}$$

Here, ρ_{el-gb} is electrical interface resistivity of Ag₂Se grain boundary phase. ρ_{el-gb} is calculated by the following formula,

$$\frac{1}{\rho_{Kapitza}} = L \frac{1}{\rho_{el-gb}} T + \frac{1}{\rho_{Lattice-gb}}$$
 (S6)

Here, $\rho_{Lattice-gb}$ is the thermal resistivity contribution from lattice at the grain boundary, $\rho_{Lattice-gb}$ parameter is used as a fitting parameter in our calculation.

$$k_t = \frac{k_g}{1 + \frac{\rho_{Kapitza}k_g}{d}} \tag{S7}$$

The power factor PF and thermoelectric figure of merit (zT) of the hammered Ag₂Se samples with different grain sizes are calculated based on the above calculated Seebeck coefficient, electrical conductivity, and thermal conductivity.

$$PF = S_t^2 \sigma_t \tag{S8}$$

$$zT = \frac{S_t^2 \sigma_t}{k_t} T \tag{S9}$$

Here, T is the absolute temperature, in our study, only room temperature is considered.

Table S1. Calculated parameters for Ag₂Se single crystal parallel to (201) plane.

Parameters	Value	Reference
S_g	-147 μV/K	[1]
k_g	1.31 W/mK	[1]
σ_g	1.01*10 ⁵ S/m	[1]

Table S2. Calculated parameters for Ag₂₁Se single crystal perpendicular to (201) plane.

Parameters	Value	Reference
${\mathcal S}_g$	-122 μV/K	[1]
k_g	1.03 W/mK	[1]
σ_g	1.51*10 ⁵ S/m	[1]

Table S3. Calculated parameters for Ag₂Se polycrystalline.

Parameters	Value	Reference
S_t	-170 μV/K	[2]
k_t	0.92 W/mK	[2]

Table S4. Fitting parameter $\rho_{Lattice-gb}$ values.

Ag ₂ Se parallel to (201)	Ag ₂ Se vertical to (201)	average of single crystal
plane	plane	Ag ₂ Se parallel and
		vertical to (201) plane
1.5*10 ^{-6.5}	1.4*10 ⁻⁷	1.5*10 ⁻⁸
1.5*10 ⁻⁶	1.4*10-8	1.5*10-6
1.5*10 ⁻⁴	1.4*10-6	1.5*10 ⁻⁷

Molecular dynamics (MD) simulation

The computational domain for MD simulations had x/y/z dimensions of 10 nm, 10 nm, and 100 nm, respectively. Both the hot and cold ends are geometrically 1 nm*1 nm*1 nm.

Reference

- [1] Lin S, Guo L, Wang X, et al. Revealing the promising near-room-temperature thermoelectric performance in Ag₂Se single crystals[J]. Journal of Materiomics, 2023, 9(4): 754-761.
 - [2] Kleinhanns T, Milillo F, Calcabrini M, et al. A Route to High Thermoelectric Performance: Solution Based Control of Microstructure and Composition in Ag₂Se[J]. Advanced Energy Materials, 2024, 14(22): 2400408.